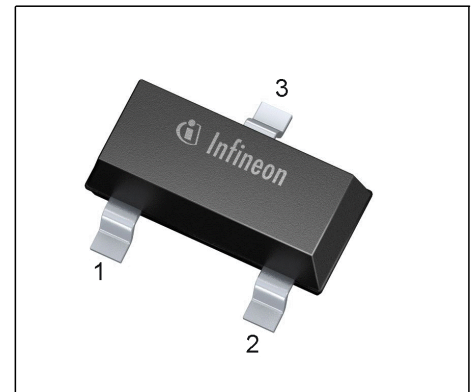


Low Noise Silicon Bipolar RF Transistor

- High linearity low noise RF transistor
- 22 dBm OP1dB and 31 dBm OIP3
@ 900 MHz, 8 V, 70 mA
- For UHF / VHF applications
- Driver for multistage amplifiers
- For linear broadband and antenna amplifiers
- Collector design supports 5 V supply voltage
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BFR106	R7s	1=B	2=E	3=C	SOT23

Maximum Ratings at $T_A = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_A = 25\text{ °C}$ $T_A = -55\text{ °C}$	V_{CEO}	16 15	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	3	
Collector current	I_C	210	mA
Base current	I_B	21	
Total power dissipation ¹⁾ $T_S \leq 76\text{ °C}$	P_{tot}	700	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{Stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	105	K/W

¹⁾ T_S is measured on the collector lead at the soldering point to the pcb

²⁾ For calculation of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	15	-	-	V
Collector-emitter cutoff current $V_{CE} = 20\text{ V}$, $V_{BE} = 0$ $V_{CE} = 10\text{ V}$, $V_{BE} = 0$	I_{CES}	-	-	1	μA
Collector-base cutoff current $V_{CB} = 10\text{ V}$, $I_E = 0$	I_{CBO}	-	1	30	nA
Emitter-base cutoff current $V_{EB} = 2\text{ V}$, $I_C = 0$	I_{EBO}	-	1	30	
DC current gain $I_C = 70\text{ mA}$, $V_{CE} = 8\text{ V}$, pulse measured	h_{FE}	70	100	140	-

Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 70\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 500\text{ MHz}$	f_T	3.5	5	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.85	1.2	pF
Collector emitter capacitance $V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.27	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	3.9	-	
Minimum noise figure $I_C = 20\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $f = 900\text{ MHz}$ $I_C = 20\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $f = 1.8\text{ GHz}$	NF_{min}	-	1.8	-	dB
		-	3	-	

Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

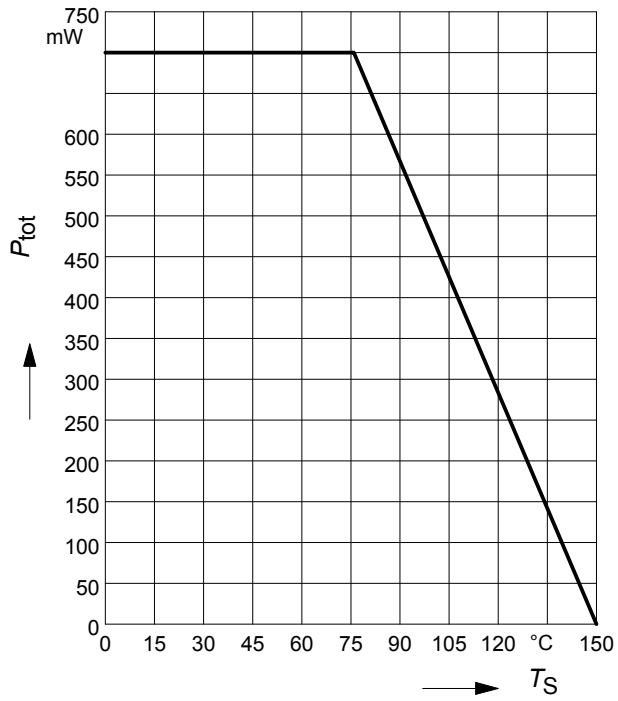
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Power gain, maximum available ¹⁾ $I_C = 70\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 900\text{ MHz}$ $I_C = 70\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	G_{ma}	-	13	-	dB
		-	8.5	-	
Transducer gain $I_C = 70\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\ \Omega$, $f = 900\text{ MHz}$ $I_C = 70\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\ \Omega$, $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	-	10.5	-	dB
		-	5	-	
Third order intercept point at output ²⁾ $V_{CE} = 8\text{ V}$, $I_C = 70\text{ mA}$, $f = 0.9\text{ GHz}$, $Z_S = Z_L = 50\ \Omega$	IP_3	-	31	-	dBm
1dB compression point $I_C = 70\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\ \Omega$, $f = 0.9\text{ GHz}$	P_{-1dB}	-	22	-	

$$^1G_{ma} = |S_{21e}| / |S_{12e}| (k - (k^2 - 1)^{1/2})$$

²⁾ IP_3 value depends on termination of all intermodulation frequency components.

Termination used for this measurement is $50\ \Omega$ from 0.1 MHz to 6 GHz

Total power dissipation $P_{\text{tot}} = f(T_S)$

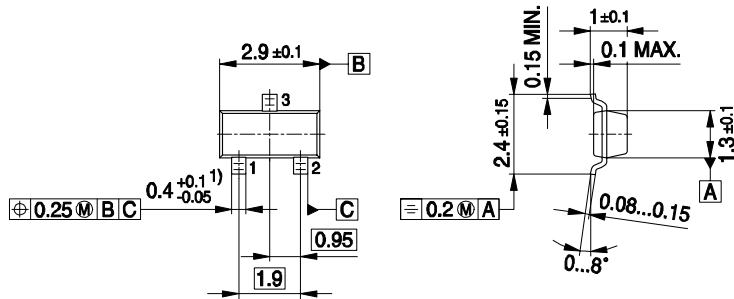


SPICE GP Model

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models.

Please consult our website and download the latest versions before actually starting your design.

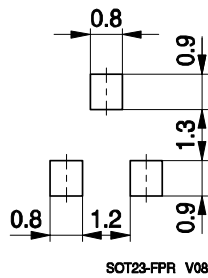
Package Outline



1) Lead width can be 0.6 max. in dambar area

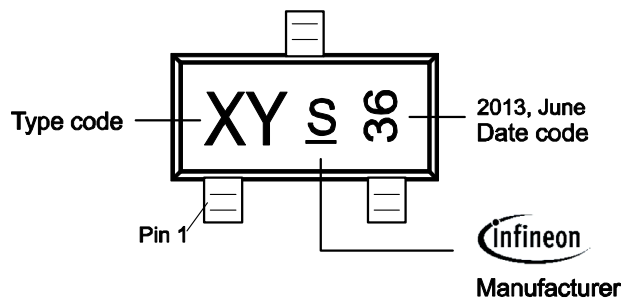
SOT23-PO V08

Foot Print



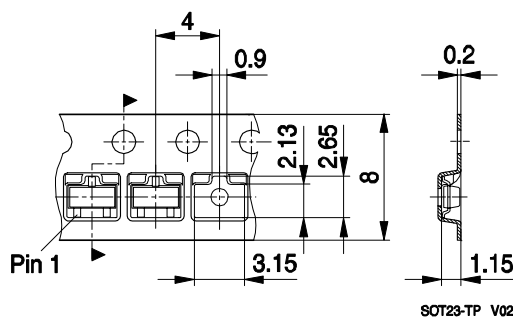
SOT23-FPR V08

Marking Layout



Standard Packing

Reel o 180 mm: 3.000 Pieces / Reel
 Reel o 330 mm = 10.000 Pieces / Reel



SOT23-TP V02

Edition 2009-11-16

**Published by
Infineon Technologies AG
81726 Munich, Germany**

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